

## Features

- Low drain-source on-resistance:  $R_{DS(ON)}=0.54\Omega$  (typ)
- Easy to control gate switching
- Enhancement mode:  $V_{th} = 2\text{V}$  to  $4\text{V}$
- 100% avalanche tested
- RoHS compliant

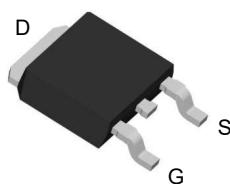
## Key Performance Parameters



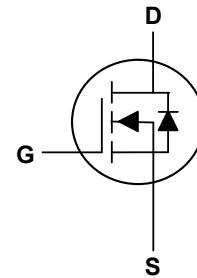
Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	700	V
$R_{DS(ON),max}$	600	mΩ
$I_D$	8	A
$Q_{g,typ}$	8	nC
$I_{DM}$	24	A

## Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Charger, Lighting



TO-252 Top View



## Absolute Maximum Ratings( $T_c=25^\circ\text{C}$ , unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	$V_{DS}$	700	V
Gate-Source Voltage	$V_{GS}$	$\pm 30$	V
Continuous Drain Current <sup>1</sup>	$I_D$	8	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	24	A
Single Pulse Avalanche Energy <sup>3</sup>	$E_{AS}$	624	mJ
Total Power Dissipation <sup>4</sup>	$P_D$	86	W
Storage Temperature Range	$T_{STG}$	-55 to 150	°C
Operating Junction Temperature Range	$T_J$	-55 to 150	°C

## Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance Junction-Ambient (Max)	$R_{\theta JA}$	62	°C/W
Thermal Resistance Junction-Case (Max)	$R_{\theta JC}$	1.45	°C/W

**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}$ , $I_D=10\text{mA}$	700	---	---	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}$ , $I_D=10\text{A}$	---	540	600	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}$ , $I_D = 250\text{\mu A}$	2.5	---	4.5	V
Drain-Source Leakage Current	$I_{\text{DSS}}$	$V_{\text{DS}}=700\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $T_J=25^\circ\text{C}$	---	---	1	$\text{\mu A}$
Gate-Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 30\text{V}$ , $V_{\text{DS}}=0\text{V}$	---	---	$\pm 100$	nA
Gate Resistance	$R_G$	$f = 1.0\text{MHz}$ , open drain	---	24	---	$\Omega$
Total Gate Charge	$Q_g$	$V_{\text{DD}}=400\text{V}$ , $V_{\text{GS}}=10\text{V}$ , $I_D=3\text{A}$	---	8	---	nC
Gate-Source Charge	$Q_{\text{gs}}$		---	2.6	---	
Gate-Drain Charge	$Q_{\text{gd}}$		---	1.7	---	
Turn-On Delay Time	$T_{\text{d(on)}}$	$V_{\text{DD}}=400\text{V}$ , $V_{\text{GS}}=10\text{V}$ , $R_G=6.8\Omega$ , $I_D=3\text{A}$	---	26.8	---	ns
Rise Time	$T_r$		---	24.8	---	
Turn-Off Delay Time	$T_{\text{d(off)}}$		---	128	---	
Fall Time	$T_f$		---	21	---	
Input Capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=50\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=10\text{kHz}$	---	595	---	pF
Output Capacitance	$C_{\text{oss}}$		---	76	---	
Reverse Transfer Capacitance	$C_{\text{rss}}$		---	3.6	---	

**Drain-Source Diode Characteristics**

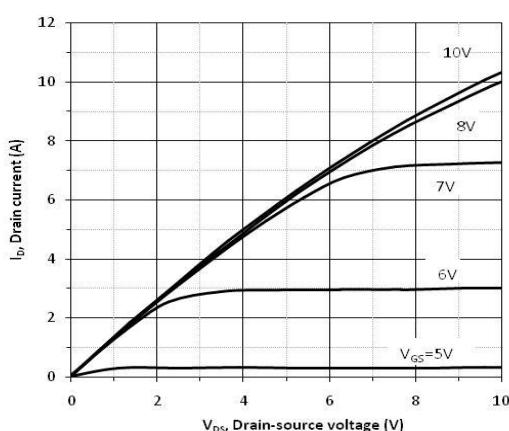
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Diode Forward Voltage <sup>2</sup>	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}$ , $I_F=1\text{A}$ , $T_J=25^\circ\text{C}$	---	0.76	---	V
Reverse recovery time	$t_{\text{rr}}$	$VR=400\text{V}$ , $IF=3\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$	---	174	---	ns
Reverse recovery charge	$Q_{\text{rr}}$		---	1.2	---	$\mu\text{C}$
Peak reverse recovery current	$I_{\text{rrm}}$		---	13.5	---	A

**Note:**

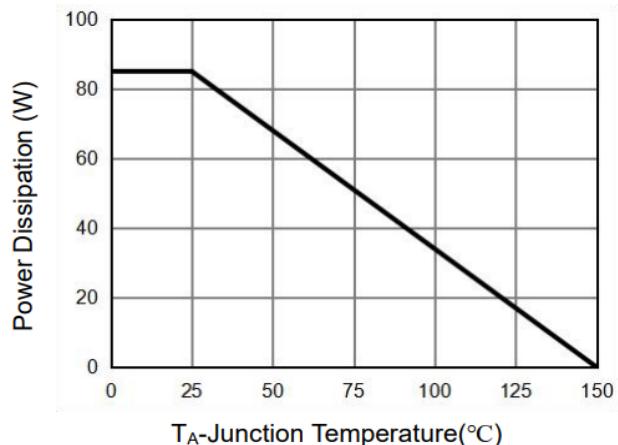
1. Limited by  $T_{j,\text{max}}$ . Maximum Duty Cycle D = 0.50
2. Pulse width  $t_p$  limited by  $T_{j,\text{max}}$
3. Identical low side and high side switch with identical  $R_G$

## Typical Characteristics

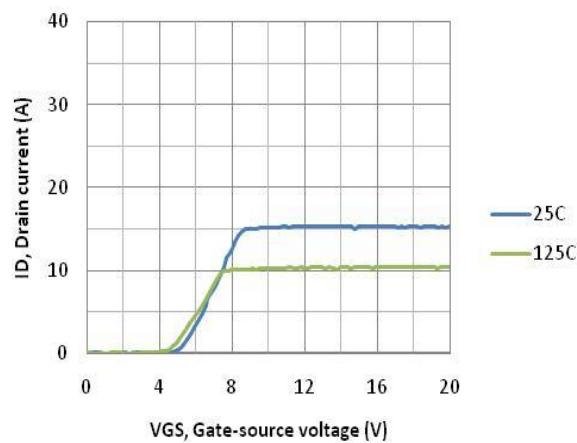
**Diagram 1: Typ. output characteristics**



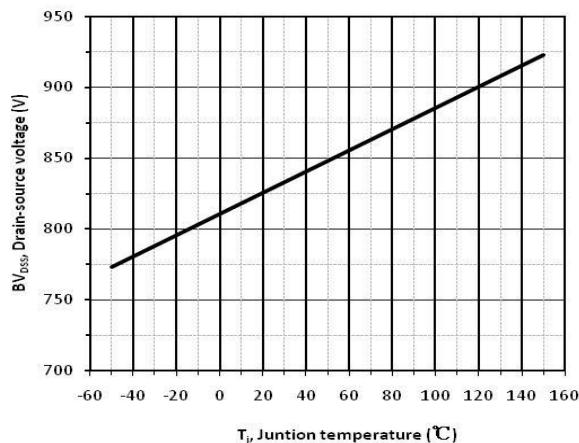
**Diagram 2: Maximum Power Dissipation**



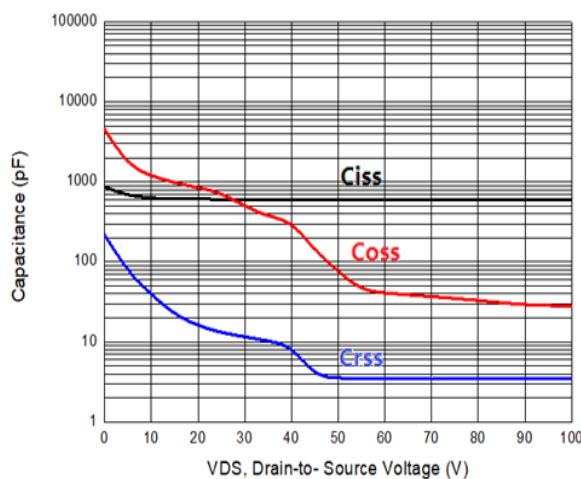
**Diagram 3: Typ. transfer characteristics**



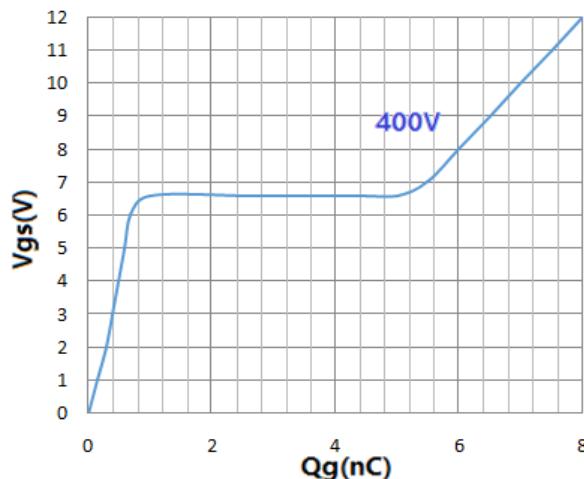
**Diagram 4: Drain-source breakdown voltage**



**Diagram 5: Typ. capacitances**



**Diagram 6: Typ. gate charge**



**Table 7 Diode characteristics**

Test circuit for diode characteristics	Diode recovery waveform
<p><math>R_{G1} = R_{G2}</math></p>	

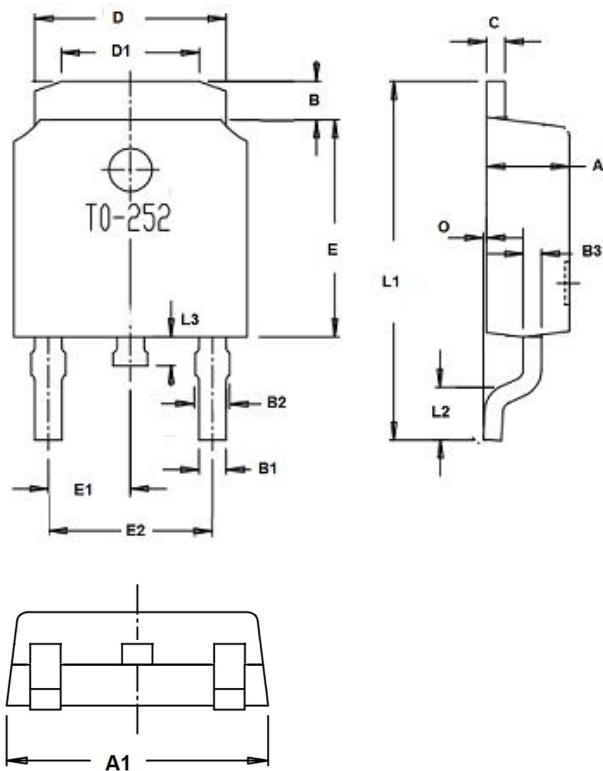
**Table 8 Switching times**

Switching times test circuit for inductive load	Switching times waveform

**Table 9 Unclamped inductive load**

Unclamped inductive load test circuit	Unclamped inductive waveform

### TO-252 Package Outline Dimensions



Dim.	Min.	Max.
A	2.1	2.5
A1	6.3	6.9
B	0.96	1.42
B1	0.74	0.86
B2	0.74	0.94
C	Typ0.5	
D	5.33	5.53
D1	3.65	4.05
E	6.0	6.2
E1	Typ2.29	
E2	Typ4.58	
O	0	0.15
L1	9.9	10.5
L2	Typ1.65	
L3	0.6	1.0
All Dimensions in millimeter		



## **Printing Information**

XXXXXXX

====Material Code

XXYY

====XX Representative Year  
YY Representative Weeks